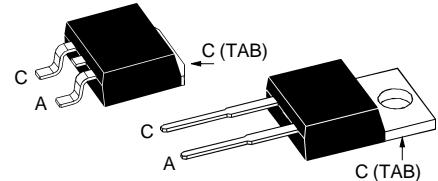


Power Schottky Rectifier

I_{FAV} = 16 A
V_{RRM} = 100 V
V_F = 0.64 V

V _{RSM}	V _{RRM}	Type
V	V	
100	100	DSS 16-01A
		DSS 16-01AS

TO-263 AB
(AS-Type)TO-220 AC
(A-Type)

A = Anode, C = Cathode , TAB = Cathode

Symbol	Conditions	Maximum Ratings	
I _{FRMS}		35	A
I _{FAV}	T _C = 155°C; rectangular, d = 0.5	16	A
I _{FSM}	T _{VJ} = 45°C; t _p = 10 ms (50 Hz), sinew	230	A
E _{AS}	I _{AS} = 9.5 A; L = 180 µH; T _{VJ} = 25°C; non repetitive	10	mJ
I _{AR}	V _A = 1.5 • V _{RRM} typ.; f=10 kHz; repetitive	1	A
(dv/dt) _{cr}		5000	V/µs
T _{VJ}		-55...+175	°C
T _{VJM}		175	°C
T _{stg}		-55...+150	°C
P _{tot}	T _C = 25°C	105	W
M _d	mounting torque (A-Type only)	0.4...0.6	Nm
Weight	typical	2	g

Symbol	Conditions	Characteristic Values	
		typ.	max.
I _R ①	T _{VJ} = 25°C V _R = V _{RRM} T _{VJ} = 125°C V _R = V _{RRM}	0.5 5	mA mA
V _F	I _F = 15 A; T _{VJ} = 125°C I _F = 15 A; T _{VJ} = 25°C I _F = 30 A; T _{VJ} = 125 °C	0.64 0.79 0.76	V V V
R _{thJC} R _{thCH}		0.5	1.4 K/W K/W

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
 Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

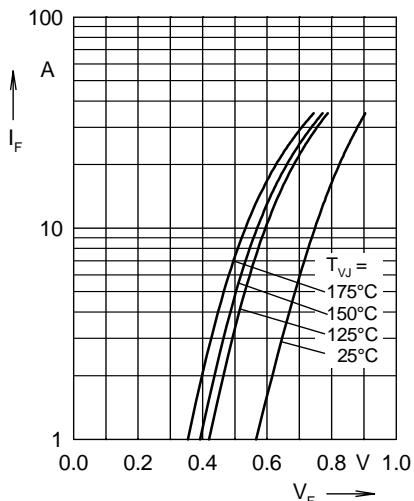


Fig. 1 Maximum forward voltage drop characteristics

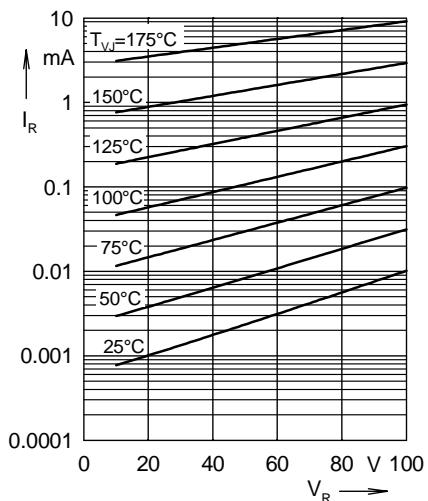


Fig. 2 Typ. value of reverse current I_R versus reverse voltage V_R

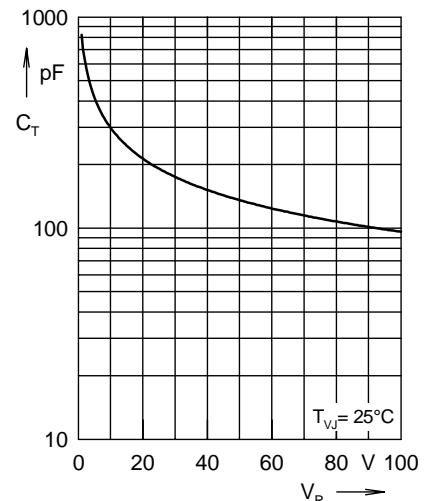


Fig. 3 Typ. junction capacitance C_T versus reverse voltage V_R

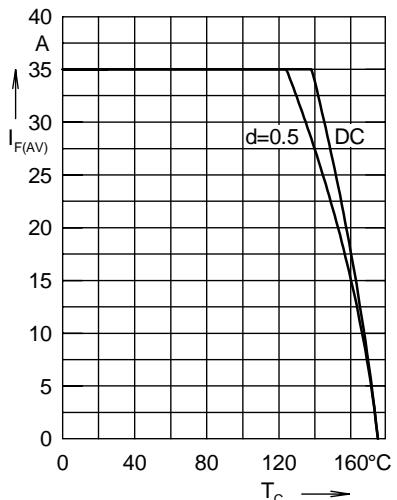


Fig. 4 Average forward current $I_{F(AV)}$ versus case temperature T_C

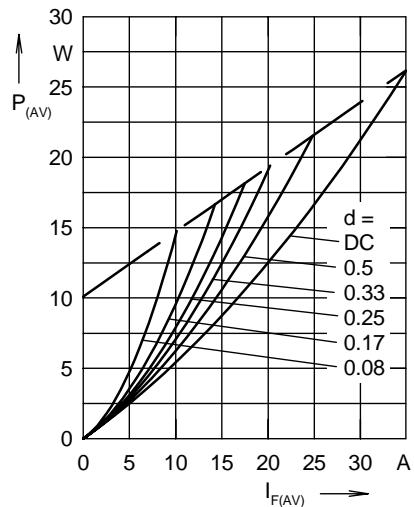


Fig. 5 Forward power loss characteristics

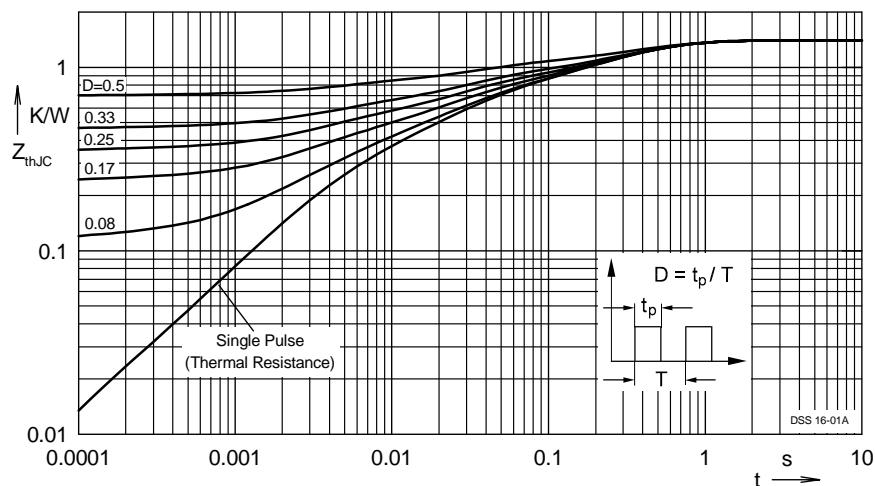


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode